

4. (Amended) The semiconductor-producing/examining device according to claim 1,  
 wherein on a face of said ceramic substrate, which is the face opposite to the face for  
 processing the semiconductor,

the connection between said conductor layer and said external terminal, or  
 the connection between said another conductor layer and said external terminal  
 is performed.

Please add new Claims 5-8 as follows:

5. (New) The semiconductor-producing/examining device according to claim 2,  
 wherein

the connection between said conductor layer and said external terminal, or  
 the connection between said another conductor layer and said external terminal  
 is performed through a non-oxidizable metal layer.

6. (New) The semiconductor-producing/examining device according to claim 2,  
 wherein on a face of said ceramic substrate, which is the face opposite to the face for

processing the semiconductor,

the connection between said conductor layer and said external terminal, or  
 the connection between said another conductor layer and said external terminal  
 is performed.

7. (New) The semiconductor-producing/examining device according to claim 3,  
 wherein on a face of said ceramic substrate, which is the face opposite to the face for  
 processing the semiconductor,

the connection between said conductor layer and said external terminal, or  
 the connection between said another conductor layer and said external terminal